# PBSS5360PAS

## 60 V, 3A PNP low VCEsat (BISS) transistor

12 October 2015

Product data sheet

### 1. General description

PNP low V<sub>CEsat</sub> Breakthrough in a Small Signal (BISS) transistor, encapsulated in an ultra thin DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package with medium power capability and visible and soldarable side pads.

NPN complement: PBSS4360PAS

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain ( $h_{FE}$ ) at high  $I_C$
- High efficiency due to less heat generation
- High temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) area requirements
- Leadless small SMD plastic package with soldarable side pads
- Exposed heat sink for excellent thermal and electrical conductivity
- Suitable for Automatic Optical Inspection (AOI) of solder joint
- AEC-Q101 qualified

## 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-60	V
I <sub>C</sub>	collector current		-	-	-3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-6	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	87	150	mΩ



## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	3
2	Е	emitter		1—
3	С	collector	Transparent top view  DFN2020D-3 (SOT1061D)	2 sym013

## 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS5360PAS	DFN2020D-3	DFN2020D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061D			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5360PAS	EA

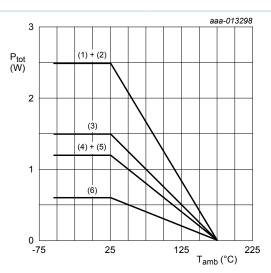
## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-80	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-60	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-8	V
I <sub>C</sub>	collector current			-	-3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-6	Α
I <sub>B</sub>	base current			-	-500	mA
I <sub>BM</sub>	peak base current			-	-1	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.6	W
			[2][3]	-	1.2	W
			[4]	-	1.5	W
			[5][6]	-	2.5	W
T <sub>j</sub>	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.
- [6] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



- (1) Ceramic PCB, single-sided copper, standard footprint
- (2) FR4 PCB, 4-layer copper, 1 cm<sup>2</sup>
- (3) FR4 PCB, single-sided copper, 6 cm<sup>2</sup>
- (4) FR4 PCB, single-sided copper, 1 cm<sup>2</sup>
- (5) FR4 PCB, 4-layer copper, standard footprint
- (6) FR4 PCB, single-sided copper, standard footprint

Fig. 1. Power derating curves

#### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	[2]	[1]	-	-	250	K/W
	from junction to ambient		[2][3]	-	-	125	K/W
			[4]	-	-	100	K/W
			[5][6]	-	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [5] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [6] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.

4 / 17

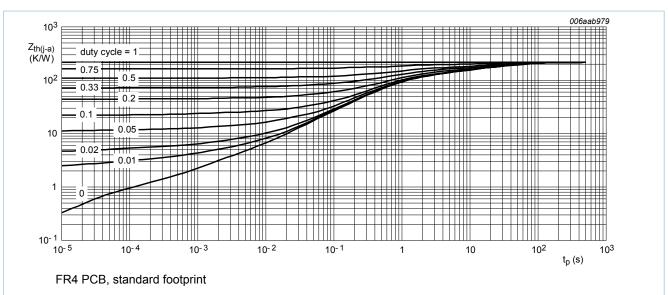


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

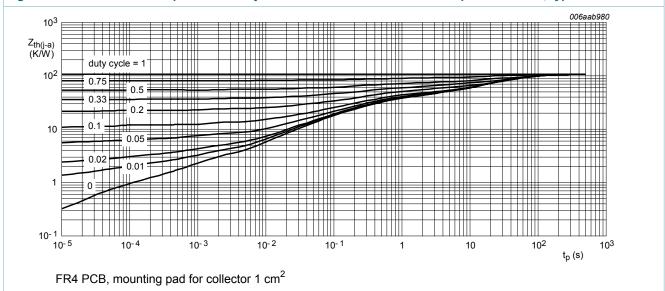


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

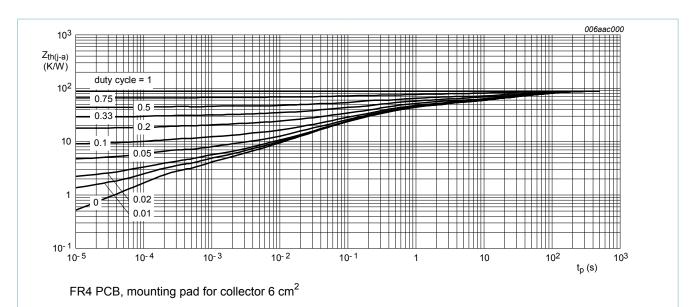


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

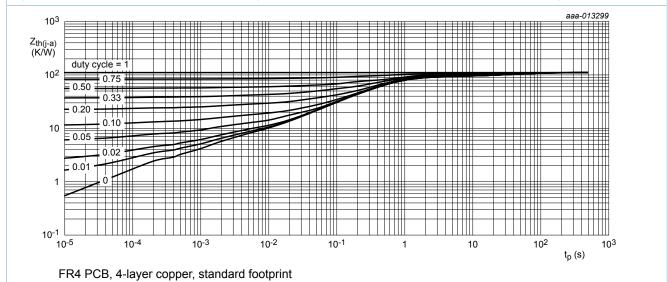


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

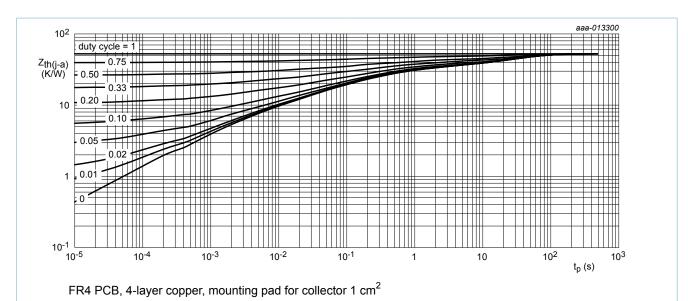


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

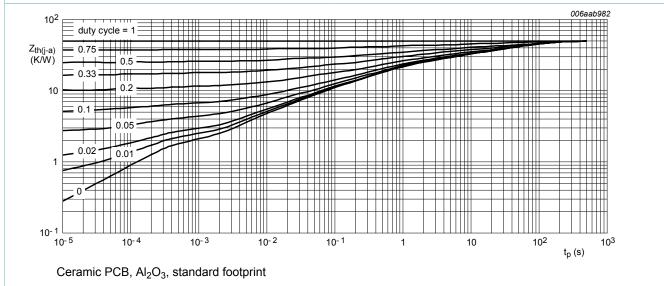


Fig. 7. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

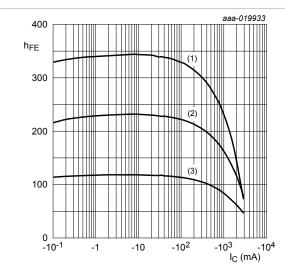
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -64 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -64 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -48 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -6.4 V; $I_{C}$ = 0 A; $T_{amb}$ = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -5 V; $I_{C}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	150	250	-	
		$V_{CE}$ = -5 V; $I_C$ = -500 mA; pulsed;	130	220	-	
		$t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb} = 25 \ ^{\circ}C$	120	200	-	
		$V_{CE} = -5 \text{ V; } I_{C} = -2 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	100	160	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -3 A; pulsed; $t_{p} \le 300 \text{ μs}; \delta \le 0.02; T_{amb}$ = 25 °C	80	125	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = -0.5 A; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 °C$	-	-55	-100	mV
		$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 °C$	-	-95	-170	mV
		$I_{C}$ = -2 A; $I_{B}$ = -200 mA; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 °C$	-	-170	-320	mV
		$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p \le 300 \ \mu s$ ; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-260	-450	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance		-	87	150	mΩ
$V_{BEsat}$	base-emitter saturation voltage	$I_{C}$ = -2 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 °C$	-	-0.9	-1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -5 \text{ V; } I_{C} = -1 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	-	-0.8	-1	V
t <sub>d</sub>	delay time	I <sub>C</sub> = -2 A; I <sub>Bon</sub> = -0.1 A; I <sub>Boff</sub> = 0.1 A;	-	12	-	ns
t <sub>r</sub>	rise time	T <sub>amb</sub> = 25 °C	-	95	-	ns
t <sub>on</sub>	turn-on time		-	107	-	ns
t <sub>s</sub>	storage time		-	160	-	ns
t <sub>f</sub>	fall time		-	50	-	ns
t <sub>off</sub>	turn-off time		-	210	-	ns
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	65	120	-	MHz

PBSS5360PAS

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$	-	28	32	pF
		f = 1 MHz; T <sub>amb</sub> = 25 °C				



 $V_{CE} = -2 V$ 

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 8. DC current gain as a function of collector current; typical values

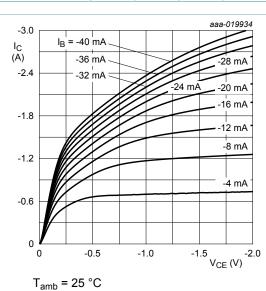
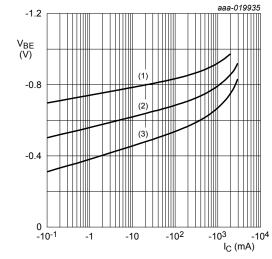


Fig. 9. Collector current as a function of collectoremitter voltage; typical values



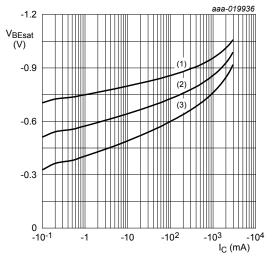
 $V_{CE} = -2 V$ 

(1) 
$$T_{amb} = -55$$
 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb}$$
 = 100 °C

Fig. 10. Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 20$$

(1) 
$$T_{amb} = -55$$
 °C

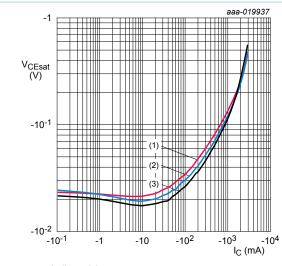
(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values

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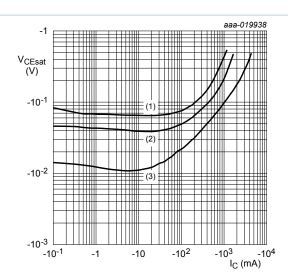
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values



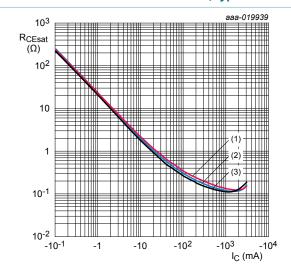
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values



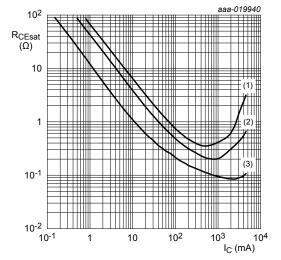
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

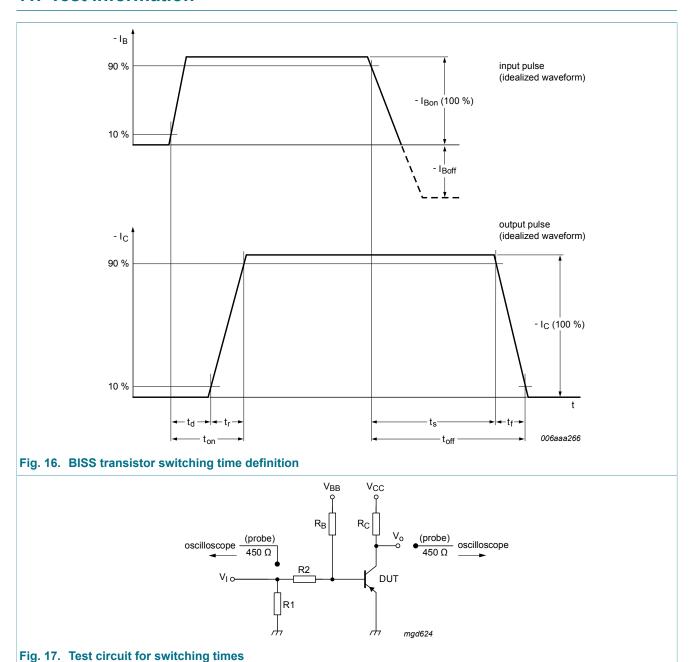
(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 15. Collector-emitter saturation resistance as a function of collector current; typical values

### 11. Test information

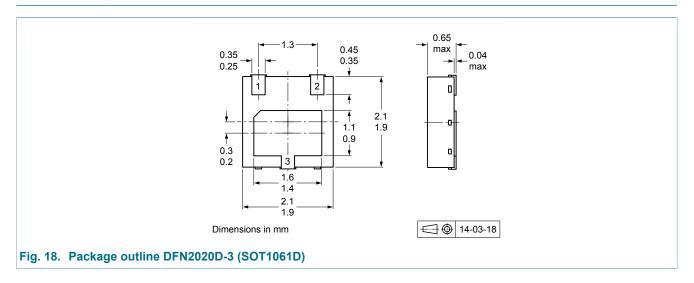


### 11.1 Quality information

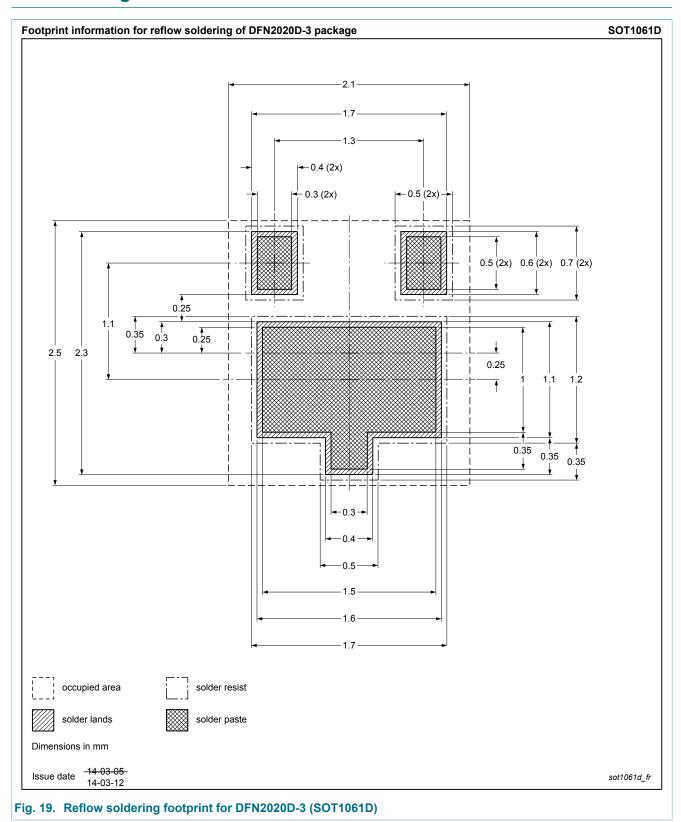
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

**Product data sheet** 

## 12. Package outline



## 13. Soldering



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## 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5360PAS v.1	20151012	Product data sheet	-	-

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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## 16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	8
11	Test information	11
11.1	Quality information	11
12	Package outline	12
13	Soldering	13
14	Revision history	14
15	Legal information	15
15.1	Data sheet status	15
15.2	Definitions	15
15.3	Disclaimers	15
15.4	Trademarks	16

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